Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	31	calculat\$3 with (mutual adj conductance)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/08/30 15:06
L2	3	L1 same ratio	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR .	ON	2007/08/30 14:54
L3		L2 same input	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON.	2007/08/30 14:54
L4	3	L3 same ac	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/08/30 14:54
L5	3	L4 same frequency	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/08/30 14:54
L6		conductance same ratio same (amplitude near5 current) same (amplitude near5 input)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/08/30 15:17
L7	1	("20060107241").PN.	US-PGPUB; USPAT; JPO	OR	OFF	2007/08/30 15:18
L8	1	L7 and (compar\$5 same dependen\$3)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/08/30 15:20
L9	1	L7 and (compar\$5 same dependen\$3)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/08/30 15:30
L10	888	mosfet and ((drain near3 dependen\$3) or (substrate near3 dependen\$3))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/08/30 15:40

L11	11379	((drain near3 dependen\$3) or (substrate near3 dependen\$3))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/08/30 15:40
L12	385	L11 same frequency	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/08/30 16:42
L13	385	L11 same frequenc\$3	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/08/30 15:40
L14	35	L13 and mosfet	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON ·	2007/08/30 15:46
L15	452	conductance same frequenc\$3 same current same input	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/08/30 15:56
L16	12	(calculat\$3 near3 conductance) same frequenc\$3 same current same input	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/08/30 15:57
L17	90	(calculat\$3 near3 conductance) same frequenc\$3	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/08/30 15:57
L18	. 3	L17 same mosfet	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/08/30 15:57
L19	9	L17 and mosfet	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/08/30 15:59
L20	2	(("5917333") or ("5317275")).PN.	US-PGPUB; USPAT; JPO	OR	OFF	2007/08/30 16:07

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L21	3	(("7132703") or ("6734501") or ("5990741")).PN.	US-PGPUB; USPAT; JPO	OR	OFF	2007/08/30 16:10
L22	1	("20060107241").PN.	US-PGPUB; USPAT; JPO	OR	OFF	2007/08/30 16:16
L23	1	L22 and (compar\$6 same dependen\$3)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/08/30 16:19
L24	1053	calculat\$3 near5 conductance	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/08/30 16:43
L25	5	L24 same (ratio with current with input)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/08/30 16:37
L26	5	L24 same (ratio with current with input)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/08/30 16:41
L27	5	L24 same (ratio same current same input)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/08/30 16:42
L28	1523	calculat\$3 with conductance	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/08/30 16:51
L29	92	L28 with ratio	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/08/30 16:44
L30	16	L29 same frequenc\$4	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/08/30 16:43

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L31	7	L29 and mosfet	US-PGPUB;	OR	OFF	2007/08/30 16:51
			USPAT; EPO; JPO; DERWENT; IBM_TDB		-	
L32	826	calculat\$3 near3 conductance	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/08/30 16:51
L33	5	L26 same ratio same (input or voltage or amplitude) same current	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/08/30 16:54
L34		L26 same ratio	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/08/30 16:54
L35	5	L26 same current	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/08/30 16:57
L36	9704	conductance same current same (voltage or input or amplitue)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/08/30 16:58
L37	9860	conductance same current same (voltage or input or amplitude)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/08/30 16:58
L38	875	L37 same ratio	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/08/30 16:58
L39	65	L38 same mosfet	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/08/30 17:18
L40	234	ac near3 conductance	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/08/30 17:18

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L41	52	L40 same voltage same current	US-PGPUB; USPAT; EPO; JPO; DERWENT;	OR	ON	2007/08/30 17:18
			IBM_TDB			
S1	4149	mosfet same soi	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/08/29 12:25
S2	865	calculat\$3 near3 conductance	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/08/29 12:30
S3	4	S1 and S2	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/08/29 13:18
S4	110935	(input near3 signal) with gate	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/08/29 13:26
S5	211	S1 and S4	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/08/29 13:26
S6	159006	measur\$6 near3 current	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON .	2007/08/29 13:26
S7	32	S5 and S6	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/08/29 13:37
S8	2	(AC adj component) near measurement near circuit	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/08/29 13:40
S9	1022	(current) near measurement near circuit	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/08/29 13:40

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S10	3947	(current) near measur\$5 near circuit	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/08/29 13:40
S11	3	(AC adj component) near measur\$5 near circuit	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/08/29 13:41
S12	3950	S10 or S11	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON .	2007/08/29 13:41
S13	428	conductance near calculat\$3	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/08/29 13:41
S14	15	S12 and S13	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/08/29 13:43
S15	106	measur\$5 near current near (source near drain)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/08/29 14:37
S16	431	conductance near calculat\$4	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/08/29 14:36
S17	0	S15 and S16	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/08/29 14:36
S18	82160	measur\$5 near current	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/08/29 14:37
S19	105	S16 and S18	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/08/29 14:37

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S20	2	S19 and S1	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/08/29 14:39
S21	82160	measur\$5 near current	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/08/29 14:39
S22	431	calculat\$4 near conductance	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/08/29 14:42
S23	21	S22 and (source same drain same gate)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/08/29 14:42
S24	9	S21 same S22	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/08/29 14:50
S25	105	S21 and S22	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/08/29 14:43
S26	13	S25 and (current same source same drain)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/08/29 14:47
S27	26	evaluat\$5 near (i-v or iv) near characteristics	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR.	ON	2007/08/29 15:43
S28	0	S27 and S1	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/08/29 15:43
S29	608	evaluat\$5 near (i-v or iv)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/08/29 15:44

S30	0	S1 and S29	US-PGPUB;	OR	ON	2007/08/29 16:20
			USPAT; EPO; JPO; DERWENT; IBM_TDB			
S31	877	(dc near3 voltage) with gate with source with drain	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/08/30 11:57
S32	2766	(apply\$3 or superimpos\$5) near (voltage) near gate	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON .	2007/08/30 11:58
S33	. 23	S31 and S32	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/08/30 12:12
S34	4308	(determin\$3 or measur\$6) with (AC near current)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/08/30 11:59
S35	1	S33 and S34	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON .	2007/08/30 11:59
S36	910658	transistor or mosfet	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/08/30 12:13
S37	71372	transistor and mosfet	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/08/30 12:13
S38	54133	transistor same mosfet	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/08/30 12:33
S39	3104	(measur\$6) near5 (ac near3 current)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/08/30 12:33

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S40	4	S39 with source with drain	US-PGPUB; USPAT; EPO; JPO;	OR	ON	2007/08/30 12:34
			DERWENT; IBM_TDB			
S41	4	S39 same (between near3 source near3 drain)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/08/30 12:38
S42	7	S39 same (source near3 drain)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/08/30 12:39
S43	. 2	S38 same S39	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/08/30 12:40
S44	99	S38 and S39	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/08/30 12:54
S45	47019	current near3 (calculat\$3 or detect\$3 or determin\$6) near3 circuit	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/08/30 12:55
S46	57481	current near3 (measur\$6 or detect\$3 or determin\$6) near3 circuit	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/08/30 12:55
S47	202	conductance near3 (calculat\$3 or detect\$3 or determin\$6) near3 circuit	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/08/30 12:56
S48	9	S46 same S47	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/08/30 12:57
S49	31	S46 and S47	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/08/30 13:02

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